

AMENDMENT

Amendments to the Claims

1. (currently amended) A process of forming a memory device,
comprising:
forming a first topology over a substrate;
~~forming a subsequent topology over the first topology;~~
forming a first ferroelectric memory structure at the first topology and after
forming the first topology; and
forming at least one subsequent ferroelectric memory structure over the
first memory structure at a corresponding at least one subsequent topology.
wherein forming a first topology includes:

forming a first dielectric layer over the substrate;
forming a first metal layer over the first dielectric layer;
forming a second dielectric layer over the first metal layer;
forming a first electrode adjacent to the second dielectric layer;
forming a second metal layer over the second dielectric layer;
forming a third dielectric layer over the second metal layer;
forming a third metal layer over the third dielectric layer; and
forming a first via between the first metal layer and the second metal layer.

(Claims 2-4 (cancelled))

PATENT APPLICATION
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5.(currently amended) The process according to claim 1 2, wherein
forming a first ferroelectric memory structure further includes:
~~forming a first electrode over the substrate;~~
forming a first ferroelectric polymer memory layer over the first electrode;
and
forming a second electrode over the first ferroelectric polymer memory
layer.

6.(currently amended) The process according to claim 1 2, wherein
forming a first ferroelectric memory structure and forming a subsequent
ferroelectric memory structure further includes:
~~forming a first electrode over the substrate;~~
forming a first ferroelectric polymer memory layer over the first electrode;
forming a second electrode over the first ferroelectric polymer memory
layer;
forming a second ferroelectric polymer memory layer over the second
electrode; and
forming a third electrode over the second ferroelectric polymer memory
layer.

[Claims 7-18 (cancelled)]

[Claims 19-29 (withdrawn)]

30.(new) A method, comprising:
forming a first electrode over a substrate;
forming a first ferroelectric oxide memory layer over the first electrode;
forming a second electrode over the first ferroelectric oxide memory layer;
and
forming a second ferroelectric oxide memory layer over the first
ferroelectric oxide memory layer, wherein the second ferroelectric oxide memory
layer is larger than the first ferroelectric oxide memory layer.

31.(new) The method of claim 30, wherein the second ferroelectric
oxide memory layer is formed so that a thickness of the first ferroelectric oxide
memory layer is substantially equal to a thickness of the second ferroelectric
oxide memory layer and so that a width of the second ferroelectric oxide memory
layer is greater than a width of the first ferroelectric oxide memory layer.

32.(new) The method of claim 30, wherein forming the first
ferroelectric oxide memory layer includes forming a ferroelectric oxide memory
layer by chemical vapor deposition, spin-on deposition, or physical vapor
deposition.

33.(new) The method of claim 30, the first electrode has a width that is
a minimum feature of a photolithography technology, selected from 0.25 micron,
0.18 micron, 0.13 micron, and 0.11 micron.

34.(new) The method of claim 30, further comprising:
forming a via coupled to the first electrode prior to forming the first
ferroelectric oxide memory layer.

35.(new) A method, comprising:
forming a structure having a cavity, wherein the structure is formed by:
forming a first electrode material over a substrate;
forming a first dielectric layer over the substrate and adjacent the
first electrode material, wherein portions of the first electrode material and
the first dielectric material define the cavity;
forming a via coupled to the first electrode; and
forming a first ferroelectric memory layer in the cavity over the first
electrode material .

36.(new) The method of claim 35, wherein forming a first ferroelectric
memory layer includes forming a first ferroelectric oxide memory layer in the
cavity.

37.(new) The method of claim 35, wherein forming a first ferroelectric
memory layer includes forming a first ferroelectric polymer memory layer in the
cavity.

38.(new) The method of claim 35, wherein forming a first ferroelectric memory layer includes forming a first ferroelectric memory layer in the cavity after forming the via.

39.(new) The method of claim 35, wherein forming a via includes forming a tungsten via coupled to the first electrode.

40.(new) The method of claim 35, further comprising:
forming a second electrode material over the first ferroelectric memory layer; and
forming a second ferroelectric memory layer in the cavity and over the first ferroelectric memory layer, wherein a volume of the second ferroelectric memory layer is greater than a volume of the first ferroelectric memory material.

41.(new) The method of claim 40, further comprising:
forming a conductive layer over the second ferroelectric memory layer;
planarizing the conductive layer; and
patterning the conductive layer to form a third electrode; and
forming an interlayer dielectric (ILD) layer over the third electrode; and
forming a third ferroelectric memory layer over the interlayer dielectric layer.

42.(new). A method, comprising:

forming a structure having a cavity, wherein the structure includes at least one dielectric layer, at least one metal layer, and at least one via; and

forming at least one ferroelectric layer in the cavity.
